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Jameco Part Number 12706TI



Data sheet acquired from Harris Semiconductor SCHS025

CMOS Dual 4-Stage Static Shift Register

With Serial Input/Parallel Output

High-Voltage Types (20-Volt Rating)

■ CD4015B consists of two identical, independent, 4-stage serial-input/paralleloutput registers. Each register has independent CLOCK and RESET inputs as well as a single serial DATA input. "Q" outputs are available from each of the four stages on both registers. All register stages are D-type, master-slave flip-flops. The logic level present at the DATA input is transferred into the first register stage and shifted over one stage at each positive-going clock transition. Resetting of all stages is accomplished by a high level on the reset line. Register expansion to 8 stages using one CD4015B package, or to more than 8 stages using additional CD4015B's is possible.

The CD4015B-series types are supplied in 16-lead hermetic dual-in-line ceramic packages (D and F suffixes), 16-lead dual-in-line plastic package (E suffix), and in chip form (H suffix).

CD4015B Types

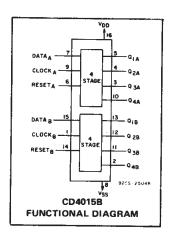
Features:

- Fully static operation
- 8 master-slave flip-flops plus input and output buffering
- 100% tested for quiescent current at 20 V
- 5-V, 10-V, and 15-V parametric ratings
- Standardized, symmetrical output characteristics
- Maximum input current of 1 μA at 18 V over full package-temperature range;
 100 nA at 18 V and 25°C
- Noise margin (full package-temperature range) =

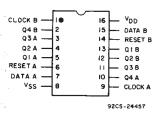
Meets all requirements of JEDEC Tentative Standard No. 13B, "Standard Specifications for Description of 'B' Series CMOS Devices"

Applications:

- Serial-input/parallel-output data queueing
- Serial to parallel data conversion
- General-purpose register



TERMINAL DIAGRAM



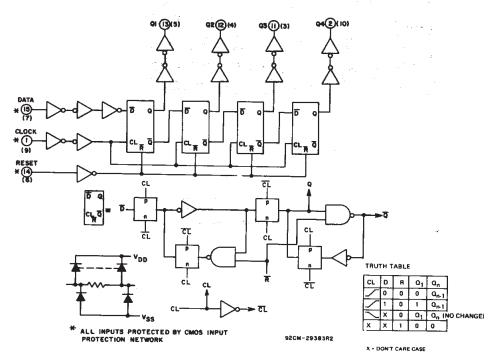


Fig. 1 - Logic diagram (1 register).

CD4015B Types

MAXIMUM RATINGS, Absolute-Maximum Values:
DC SUPPLY-VOLTAGE RANGE, (VDD)
Voltages referenced to VSS Terminal)0.5V to +20V
INPUT VOLTAGE RANGE, ALL INPUTS0.5V to V _{DD} +0.5V
DC INPUT CURRENT, ANY ONE INPUT
POWER DISSIPATION PER PACKAGE (PD):
For T _A = -55°C to +100°C
For T _A = +100°C to +125°C Derate Linearity at 12mW/°C to 200mW
DEVICE DISSIPATION PER OUTPUT TRANSISTOR
FOR TA = FULL PACKAGE-TEMPERATURE RANGE (All Package Types)
OPERATING-TEMPERATURE RANGE (TA)55°C to +125°C
STORAGE TEMPERATURE RANGE (Tstg)65°C to +150°C
LEAD TEMPERATURE (DURING SOLDERING):
At distance 1/16 ± 1/32 inch (1.59 ± 0.79mm) from case for 10s max +265°C

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Fig. 2 - Typical output low (sink) current characteristics

RECOMMENDED OPERATING CONDITIONS at $T_A = 25^{\circ}$ C, Except as Noted. For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

CHARACTERISTIC	•	V _{DD}	LIN	UNITS	
	<u> </u>	(V)	Min.	Max.	
Supply-Voltage Range (For T _A Temperature Range)	= Full Package-		3	18	V
Clock Pulse Width,	t _W CL	5 10 15	180 80 50		ns
Clock Rise and Fall Time,	t _r CL, t _f CL	5 10 15		15 6 2	μs
Clock Input Frequency,	fCL	5 10 15	DC	3 6 8.5	MHz
Data Setup Time,	^t SU	5 10 15	70 40 30	- - 	ns
Reset Pulse Width,	t _W R	5 10 15	200 80 60	1 -	ns

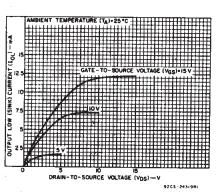
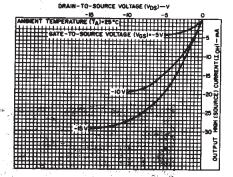


Fig. 3 — Minimum output low (sink) current characteristics.



g. 4 — Typical output high (source) current characteristics.

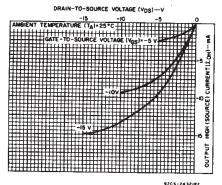


Fig. 5 — Minimum output high (source) current characteristics.

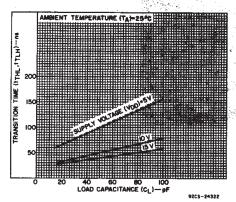


Fig. 6 — Typical transition time as a function of load capacitance.

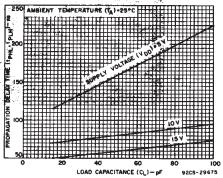
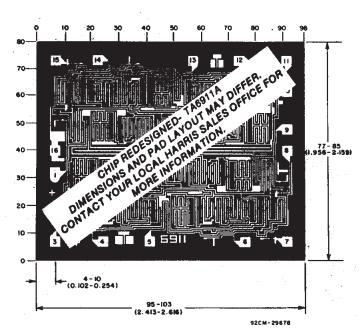


Fig. 7 — Typical propagation delay time as a function of load-capacitance.

CD4015B Types

STATIC ELECTRICAL CHARACTERISTICS

CHARACTER-	COND	HOITION	IS	LIMITS AT INDICATED TEMPERATURES (°C)											
ISTIC	Vo	VIN	VDD	-55	-40	+85	+125	Min.	+25	Max.	UNITS				
	(V)	(V)	(V)						Тур.						
Quiescent Device		0,5	5	5	5	150	150		0.04	5					
Current,	-	0,10	10	10	10	300	300	_	0.04	10	μА				
IDD Wax.		0,15	15	20	20	600	600		- 0.04	20	μ				
	-	0,20	20	100	100	3000	3000	-	0.08	100					
Output Low	0.4	0,5	5	0.64	0.61	0.42	0.36	0.51	1						
(Sink) Current	0.5	0,10	10	1.6	1.5	1.1	0.9	1.3	2.6	_]				
IOL Min.	1.5	0,15	15	4.2	4	2.8	2.4	3.4	6.8	-					
Output High	4.6	0,5	5	-0.64	-0.61	-0.42	-0.36	-0.51	-1	_	mA				
(Source)	2.5	0,5	5	-2	-1.8	-1.3	-1.15	-1.6	-3.2	-					
Current,	9.5	0,10	10	-1.6	-1.5	-1.1	-0.9	-1.3	-2.6	<u> </u>	1				
IOH Min.	13.5	0,15	15	-4.2	-4	-2.8	-2.4	-3.4	-6.8		[
Output Voltage:	-	0,5	5		. 0	.05		-	0	0.05	I				
Low-Level, VOL Max.		0,10	10		0	.05		-	0	0.05					
AOF Max.		0,15	15		0	.05	•	-	0	0.05	l v l				
Output Voltage:	-	0,5	5		4	.95		4.95	5	-	v				
High-Level,		0,10	10		9	.95		9.95	10	-					
VOH Min.	_	0,15	15		14	.95		14.95	15	-					
Input Low	0.5, 4.5	_	5		1	.5		_	_	1.5					
Voltage,	1,9	_,	10		-	3		_	_	3	1				
VIL Max.	1.5,13.5	_	15	5 4					_	4	١				
Input High	0.5, 4.5	_	5		3	3.5		3.5	_		\ \				
Voltage,	1, 9	_	10			7		7	_	_					
VIH Min.	1.5,13.5		15			11		11		_					
Input Current IIN Max.	_	0,18	18	±0.1	±0.1	±1	±1	-	±10 ⁻⁵	±0.1	μΑ				



Photograph of Chip Layout for CD4015B.

Dimensions in parentheses are in millimeters and are derived from the basic inch dimensions as indicated. Grid graduations are in mils (10⁻³ inch).

DYNAMIC ELECTRICAL CHARACTERISTICS at TA = 25°C, Input ti, ti = 20 ns, $C_{\rm L}$ = 50 pF, $R_{\rm L}$ = 200 $k\Omega$

CHARACTERISTIC	TEST CONDITIONS		UNITS		
CHARACTERISTIC	V _{DD} (V)	MIN.	TYP.	MAX.	UNITS
CLOCKED OPERATION					·
Propagation Delay Time,	5		160	320	
T _{PHL} , T _{PLH}	10	_	80	160	
	15	_	60	120	
	5	_	100	200	
Transition Time, t _{THL} , t _{TLH}	10	_	50	100	ns
	15	_	40	80	
Minimum Clock Pulse	5	_	90	180	1
Width, twCL	10	_	40	80	1
	15	—	25	50	
Clock Rise and Fall Time,	5		_	15	
t _r CL, t _f CL*	10	_		6	μs
	15		l –	2	
Minimum Data Setup Time,	5		35	70	
tSU	10		20	40	
<u> </u>	- 15		15	30 -	
	5	_	-	0	ns
Minimum Data Hold Time, t _H	10	_	–	0	
	15	_		0	
Maximum Clock Input	5	3	6	_	
Frequency, f _{CL}	10	6	12	_	MHz
	15	8.5	17		
Input Capacitance, C _{IN}	Any Input	_	5	7.5	pF
RESET OPERATION				•	•
Propagation Delay Time,	5	_	200	400	
TPHL, TPLH	10		100	200	
	15	_	80	160	
Minimum Reset Pulse Width,	5	_	100	200	ns
twR	10	_	40	80	
	15	-	30	60	

^{*}If more than one unit is cascaded t_iCL should be made less than or equal to the sum of the transition time and the fixed propagation delay of the output of the driving stage for the estimated capacitive load.

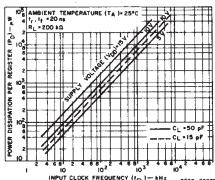


Fig. 8 - Typical power dissipation as a function of frequency.

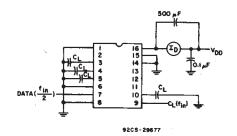


Fig. 9 - Power dissipation test circuit.

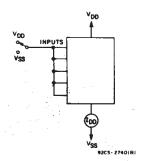
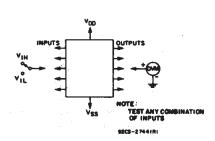


Fig. 10 - Quiescent device current test



CD4015B Types

Fig. 11 - Input voltage test circuit.

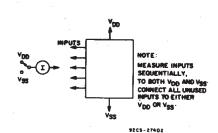


Fig. 12 - Input current test circuit.

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